

### Complementary power Darlington transistors

#### Features

- Complementary transistors in monolithic Darlington configuration
- Integrated collector-emitter antiparallel diode

#### **Applications**

- Audio power amplifier
- DC-AC converter
- General purpose switching applications

#### Description

The 2N6284 is an epitaxial-base NPN power transistor in monolithic Darlington configuration mounted in TO-3 metal case. It is inteded for general purpose amplifier and low frequency switching applications.

The complementary PNP type is 2N6287.

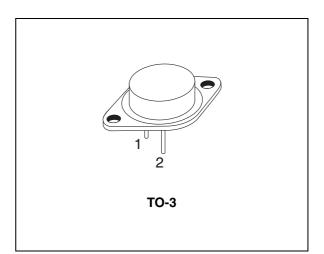
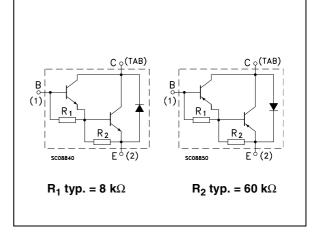


Figure 1. Internal schematic diagrams



#### Table 1. Device summary

Order code	Marking	Package	Packaging
2N6284	2N6284	TO-3	Dee
2N6287	2N6287	10-3	Bag

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Rev 3

1/8

### 1 Absolute maximum ratings

			Value	
Symbol	Parameter	NPN	2N6284	Unit
		PNP	2N6287	
V <sub>CBO</sub>	Collector-base voltage $(I_E = 0)$	100	V	
V <sub>CEO</sub>	Collector-emitter voltage ( $I_B = 0$ )	100	V	
V <sub>EBO</sub>	Emitter-base voltage $(I_C = 0)$	5	V	
۱ <sub>C</sub>	Collector current	20	А	
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	40	А	
Ι <sub>Β</sub>	Base current	0.5	А	
P <sub>tot</sub>	Total dissipation at $T_{C}$ = 25 °C	160	W	
T <sub>stg</sub>	Storage temperature	-65 to 200	°C	
TJ	Max. operating junction temperature	200	°C	

#### Table 2. Absolute maximum ratings

For PNP type voltage and current values are negative

#### Table 3. Thermal data

Symbol	Parameter		Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case Max		1.09	°C/W



### 2 Electrical characteristics

(T<sub>case</sub> = 25 °C; unless otherwise specified)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>CEV</sub>	Collector cut-off current (V <sub>BE</sub> = -1.5 V)	V <sub>CE</sub> = 100 V V <sub>CE</sub> = 100 V	T <sub>c</sub> = 150 °C			0.5 5	mA mA
I <sub>CEO</sub>	Collector cut-off current $(I_B = 0)$	V <sub>CE</sub> = 50 V				1	mA
I <sub>EBO</sub>	Emitter cut-off current $(I_{\rm C} = 0)$	V <sub>EB</sub> = 5 V				2	mA
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage $(I_B = 0)$	I <sub>C</sub> = 100 mA		100			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	I <sub>C</sub> = 10 A I <sub>C</sub> = 20 A	I <sub>B</sub> = 40 mA I <sub>B</sub> = 200 mA			2 3	V V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 20 A	I <sub>B</sub> = 200 mA			4	V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	I <sub>C</sub> = 10 A	$V_{CE} = 3 V$			2.8	V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	I <sub>C</sub> = 10 A I <sub>C</sub> = 20 A	V <sub>CE</sub> = 3 V V <sub>CE</sub> = 3 V	750 100		18000	
h <sub>fe</sub>	Small signal current gain	l <sub>C</sub> = 10 A f = 1 kHz	$V_{CE} = 3 V$	300			
C <sub>CBO</sub>	Collector-base capacitance (I <sub>E</sub> = 0)	V <sub>CB</sub> = 10 V for 2N6284 for 2N6287	f = 100 kHz			400 600	pF pF

Table 4. Electrical characteristics

1. Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$ 1.5 %

For PNP type voltage and current values are negative

57

G-535

−T<sub>C</sub>=150°C−

10 I<sub>C</sub> (A)

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T<sub>c</sub>=-55°C

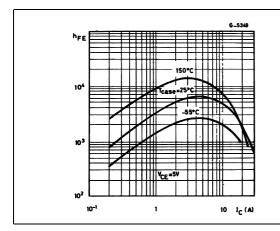
V<sub>CE</sub>=5V

DC current gain (PNP type)

1

### 2.1 Electrical characteristics (curves)

Figure 2. DC current gain (NPN type)





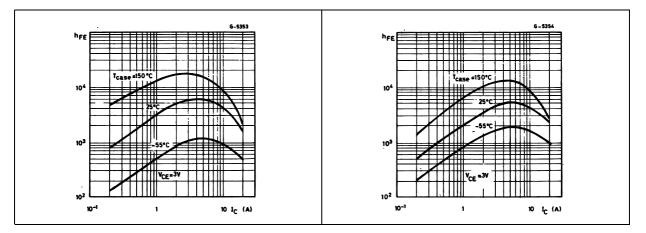
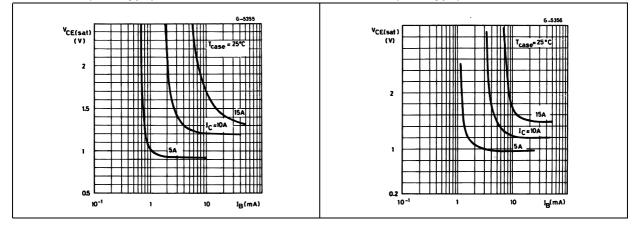


Figure 6. Collector-emitter saturation voltage Figure 7. Collector-emitter saturation voltage (NPN type) (PNP type)



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 $\mathsf{h}_{\mathsf{FE}}$ 

10000

1000 T<sub>C</sub>

100 L 0.1

Figure 5.

### 3 Package mechanical data

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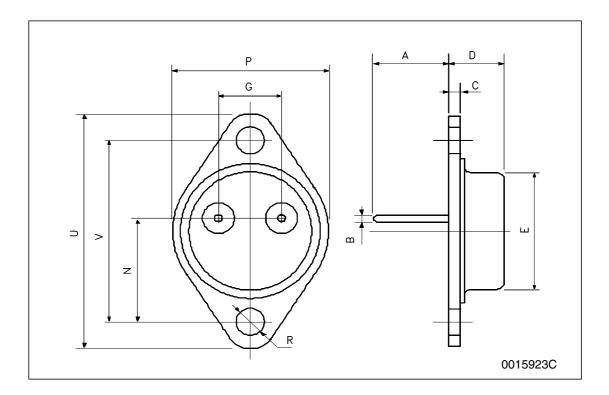
### 4 Revision history

Table 5.	Document revision history

Date	Revision	Changes
02-Mar-2000	2	
26-Jan-2009	3	Added paragraph 2.1



	TO-3 mechanical data					
DIM.		mm.				
DIM.	min.	typ	max.			
А	11.00		13.10			
В	0.97		1.15			
С	1.50		1.65			
D	8.32		8.92			
Е	19.00		20.00			
G	10.70		11.10			
Ν	16.50		17.20			
Р	25.00		26.00			
R	4.00		4.09			
U	38.50		39.30			
V	30.00		30.30			



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